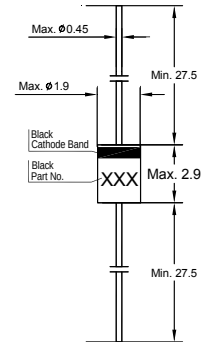


1N4148M

Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	60	V
Reverse Voltage	V_R	50	V
Average Rectified Forward Current	$I_{F(AV)}$	130	mA
Surge Forward Current at $t < 1$ s	I_{FSM}	500	mA
Power Dissipation	P_{tot}	400 ¹⁾	mW
Junction Temperature	T_j	200	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 200	$^\circ\text{C}$

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)R}$	60	-	V
Forward Voltage at $I_F = 100 \text{ mA}$	V_F	-	1.1	V
Reverse Leakage Current at $V_R = 50 \text{ V}$	I_R	-	0.5	μA
Capacitance at $V_R = 0$, $f = 1 \text{ MHz}$	C_{tot}	-	3	pF
Reverse Recovery Time at $I_F = 10 \text{ mA}$ to $I_R = 1 \text{ mA}$, $I_{rr} = 0.1 \times I_R$, $V_R = 6 \text{ V}$, $R_L = 100 \Omega$	t_{rr}	-	4	ns

